星合电子
XINGHE ELECTRONICS

LLDB3/LLDC34/LLDB4/LLDB6

SILICON BIDIRECTIONAL DIAC

FEATURES

- The three-layer, two-terminal, axial-lead, hermetically sealed diacs are designed specifically for triggering thyristors. They demonstrate low breakover current at breakover voltage as they withstand peak pulse current. The breakover symmetry is within three volts(DB3,DC34,DB4) or four volts(DB6). These diacs are intended for use in thyrisitors phase control , circuits for lamp dimming, universal motor speed control and heat control.
- JF's DB3/DC34/DB4/DB6 are bi-directional triggered diode designed to operate in conjunction with Triacs and SCR's
- High temperature soldering guaranteed:260℃/10 seconds at terminals
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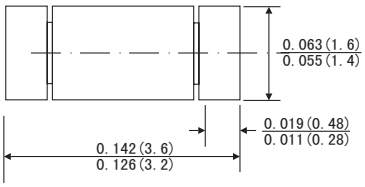
MiniMELF



Dimensions in inches and (millimeters)

MECHANICAL DATA

- *Case*: MiniMELF glass case(SOD-80)
- *Weight*: Approx. 0.05 gram

ABSOLUTE RATINGS(LIMITING VALUES)

Symbols	Parameters		Value				Units
			LLDB3	LLDC34	LLDB4	LLDB6	
P_C	Power Dissipation on Printed Circuit(L=10mm)	T_A=50℃	150				mW
I_{TRM}	Repetitive Peak on-state Current	tp=10μs f=100Hz	2.0			1.6	A
T_{STG}/T_J	Storage and Operating Junction Temperature		-40 to+125				℃

ELECTRICAL CHARACTERISTICS

Symbols	Parameters	Test Condition		Value				Units
				LLDB3	LLDC34	LLDB4	LLDB6	
V_{BO}	Breakover Voltage (Note 2)	C=22nF(Note 2) See diagram 1	Min	28	30	35	56	V
			Typ	32	34	40	60	
			Max	36	38	45	70	
| +VBO | - | -VBO |	Breakover Voltage Symmetry	C=22nF(Note 2) See diagram 1	Max	±3			±4	V
| ± △V |	Dynamic Breakover Voltage (Note1)	△I=(I_{BO} to IF=10mA) See Diagram 1	Min	5			10	V
V_O	Output Voltage (Note 1)	See Diagram 2	Min	5				V
I_{BO}	Breakover Current (Note1)	C=22nF(Note 2)	Max	100				μA
tr	Rise Time (Note1)	See Diagram 3	Typ	1.5				μs
I_B	Leakage Current (Note1)	V_B=0.5 V_{BO} max see diagram 1	Max	10				μA

Notes: 1.Electrical characteristics applicable in both forward and reverse directions.
2.Connected in parallel with the devices.

DIAGRAM 1: Current-voltage characteristics

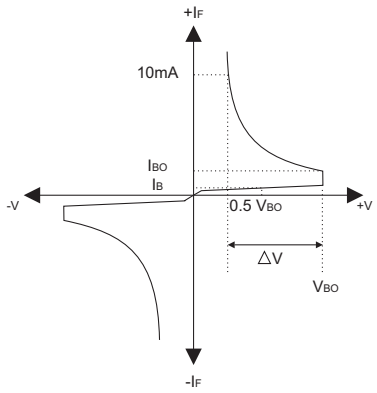


DIAGRAM 2: Test circuit for output voltage

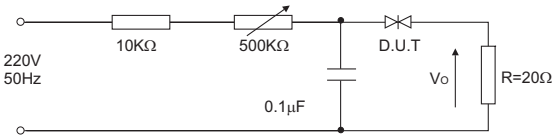


DIAGRAM 3: Test circuit see diagram2 adjust R for IP=0.5A

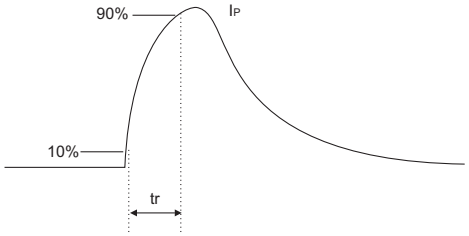


FIG.1-Power dissipation versus ambient temperature (maximum values)

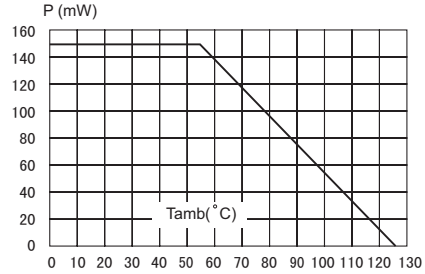


FIG.2-Relative variation of VBO versus junction temperature(typical values)

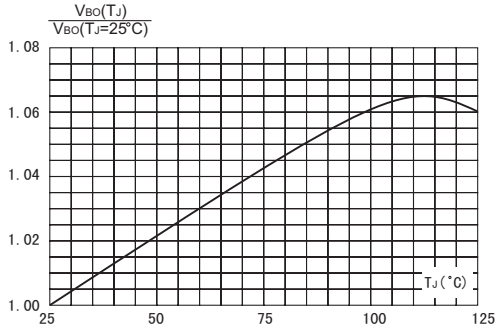


FIG.3-Peak pulse current versus pulse duration (maximum values)